



THE DATASHEET OF STPS2060CT



POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_{RRM}	60 V
V_F (max)	0.58 V

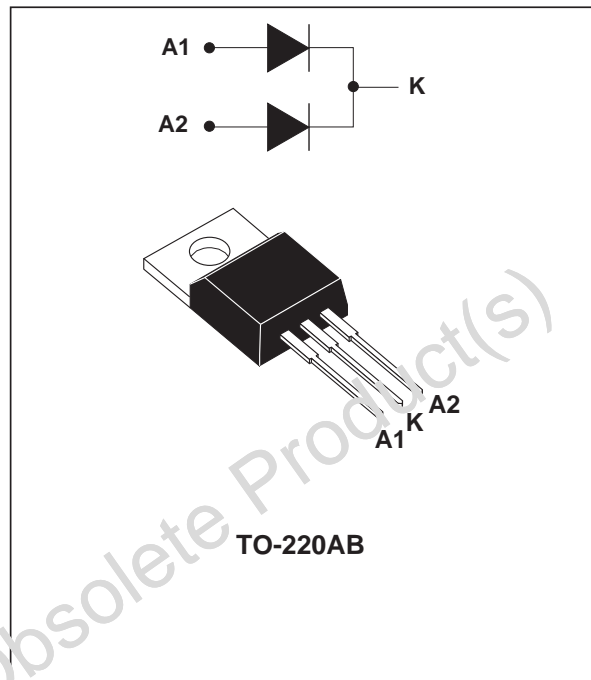
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY

DESCRIPTION

High voltage dual Schottky rectifier suited to Switch Mode Power Supplies and other Power Converters.

Packaged in TO-220AB, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	60	V
$I_{F(RMS)}$	RMS forward current	Per diode 30	A
$I_{F(AV)}$	Average forward current	$T_{case} = 120^{\circ}C$ Per diode $V_R = 60V$ Per device $\delta = 0.5$ 10 20	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\ ms$ Sinusoidal Per diode	200 A
I_{RRM}	Repetitive peak reverse current	$t_p = 2\ \mu s$ $F = 1\ kHz$ Per diode	1 A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100\ \mu s$ Per diode	1 A
T_{stg}	Storage temperature range	- 65 to + 150	$^{\circ}C$
T_j	Maximum junction temperature	150	$^{\circ}C$
dV/dt	Critical rate of rise of reverse voltage	10000	V/ μs

STPS2060CT

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6	°C/W
		Total	0.9	
$R_{th(c)}$		Coupling	0.15	°C/W

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

ELECTRICAL STATIC CHARACTERISTICS (per diode)

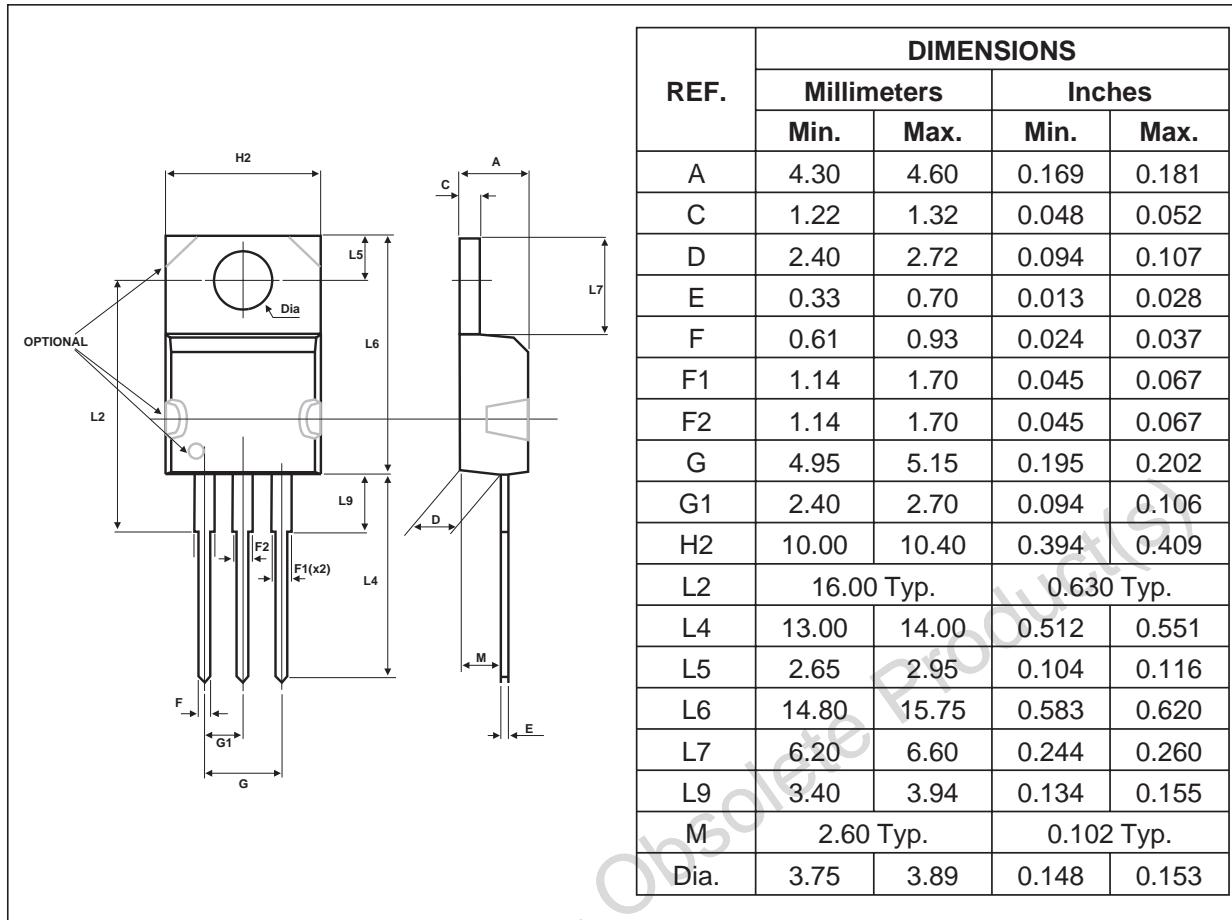
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$			70	μA
			$T_j = 125^\circ\text{C}$			33	mA
V_F^{**}	Forward voltage drop	$I_F = 20 \text{ A}$	$T_j = 125^\circ\text{C}$			0.8	V
		$I_F = 10 \text{ A}$	$T_j = 125^\circ\text{C}$		0.58	0.67	
		$I_F = 20 \text{ A}$	$T_j = 25^\circ\text{C}$			0.94	
C	Capacitance	60 V, 1MHz	$T_j = 125^\circ\text{C}$		150		pF

Pulse test : * $t_p = 5 \text{ ms}$, duty cycle < 2 %
** $t_p = 380 \mu\text{s}$, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.54 \times I_F(\text{AV}) + 0.013 \times I_F^2(\text{RMS})$$

PACKAGE MECHANICAL DATA
TO-220AB



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